# **Switching Transistor**

# **PNP Silicon**

### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	-40	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	-40	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	-600	mAdc
Collector Current – Peak	I <sub>CM</sub>	-900	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

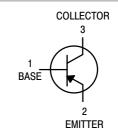
\*Transient pulses must not cause the junction temperature to be exceeded. 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



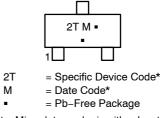
# **ON Semiconductor®**

http://onsemi.com





MARKING DIAGRAM



(Note: Microdot may be in either location)

\*Specific Device Code, Date Code or overbar orientation and/or location may vary depending upon manufacturing location. This is a representation only and actual devices may not match this drawing exactly.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBT4403LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMBT4403LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT4403LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

C	Symbol	Min	Мах	Unit	
OFF CHARACTERISTICS			•		
Collector - Emitter Breakdown Voltage	(Note 3) $(I_{\rm C} = -1.0 \text{ mAdc}, I_{\rm B} = 0)$	V <sub>(BR)CEO</sub>	-40	-	Vdc
Collector – Base Breakdown Voltage	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$	V <sub>(BR)CBO</sub>	-40	-	Vdc
Emitter – Base Breakdown Voltage	$(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Base Cutoff Current	$(V_{CE} = -35 \text{ Vdc}, V_{EB} = -0.4 \text{ Vdc})$	I <sub>BEV</sub>	-	-0.1	μAdc
Collector Cutoff Current	(V <sub>CE</sub> = $-35$ Vdc, V <sub>EB</sub> = $-0.4$ Vdc)	ICEX	-	-0.1	μAdc
ON CHARACTERISTICS		·			
DC Current Gain (Note 3) (Note 3)		h <sub>FE</sub>	30 60 100 100 20	_ _ _ 300 _	_
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>		-0.4 -0.75	Vdc	
Base – Emitter Saturation Voltage (Not	V <sub>BE(sat)</sub>	-0.75	-0.95 -1.3	Vdc	
SMALL-SIGNAL CHARACTERISTIC	S	·	-		
Current-Gain - Bandwidth Product	(I <sub>C</sub> = -20 mAdc, $V_{CE}$ = -10 Vdc, f = 100 MHz)	f <sub>T</sub>	200	-	MHz
Collector-Base Capacitance	Collector-Base Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$		-	8.5	pF
Emitter–Base Capacitance $(V_{BE} = -0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C <sub>eb</sub>	-	30	pF
Input Impedance $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		h <sub>ie</sub>	1.5	15	kΩ
/oltage Feedback Ratio $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		h <sub>re</sub>	0.1	8.0	X 10-
Small – Signal Current Gain $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		h <sub>fe</sub>	60	500	-
Output Admittance	$(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		1.0	100	μMhos
SWITCHING CHARACTERISTICS					
Delay Time	(V <sub>CC</sub> = -30 Vdc, V <sub>EB</sub> = -2.0 Vdc,	t <sub>d</sub>	-	15	200
Rise Time	$I_{\rm C} = -150 \text{ mAdc}, I_{\rm B1} = -15 \text{ mAdc})$	t <sub>r</sub>		20	ns
Storage Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc},$	t <sub>s</sub>	-	225	ns
Fall Time	I <sub>B1</sub> = I <sub>B2</sub> = -15 mAdc)		-	30	113

3. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

## SWITCHING TIME EQUIVALENT TEST CIRCUIT

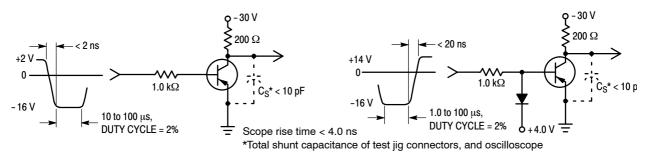
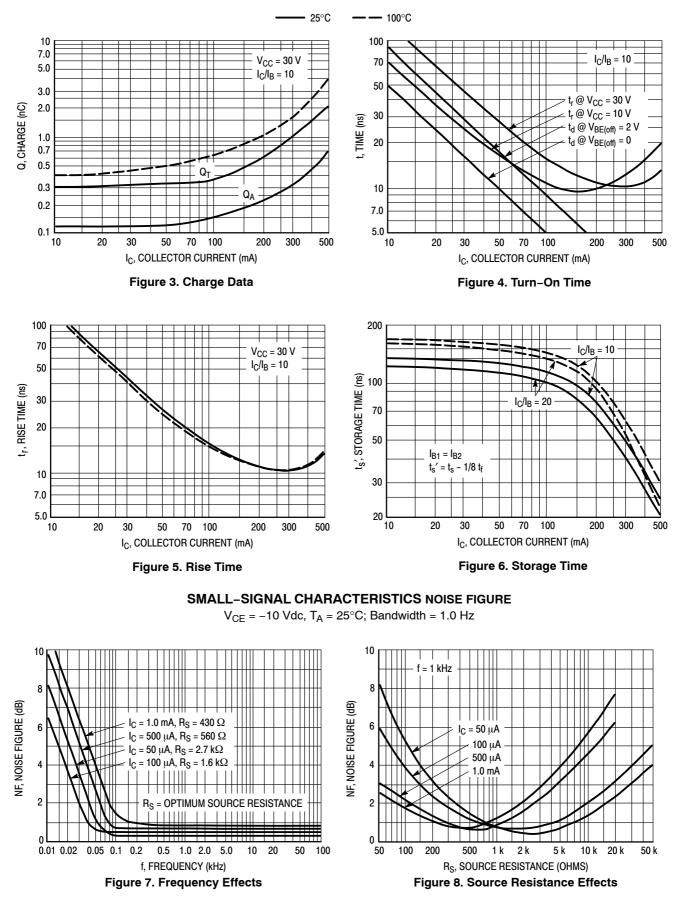


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

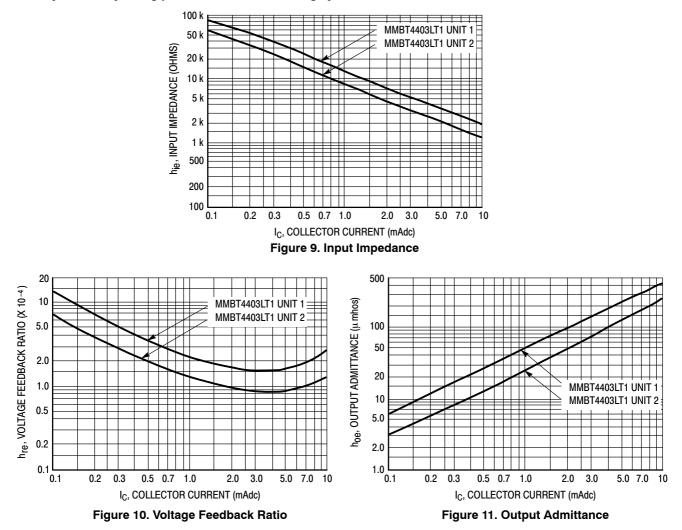
#### **TRANSIENT CHARACTERISTICS**



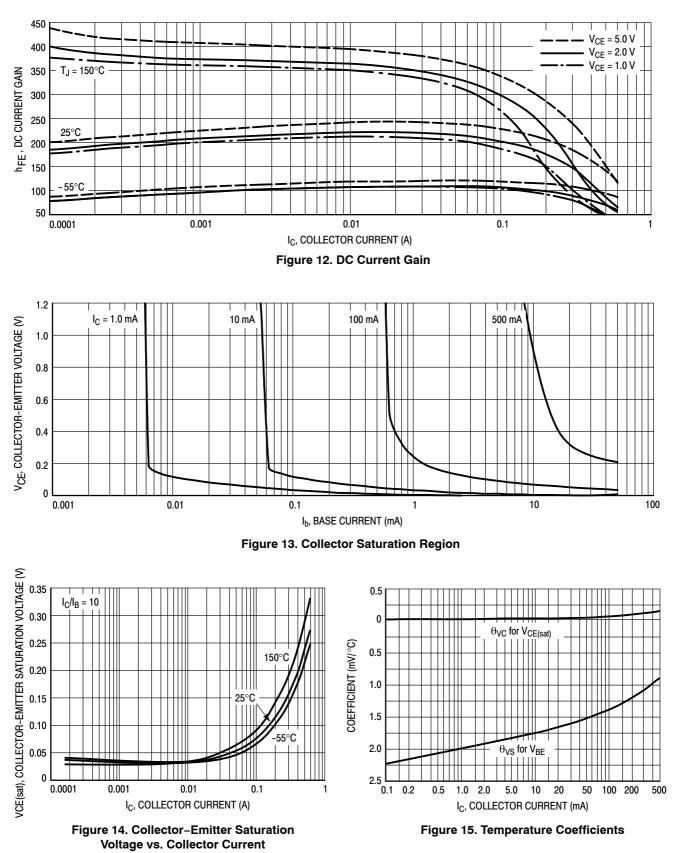
## h PARAMETERS

# $V_{CE}$ = 10 Vdc, f = 1.0 kHz, T<sub>A</sub> = 25°C

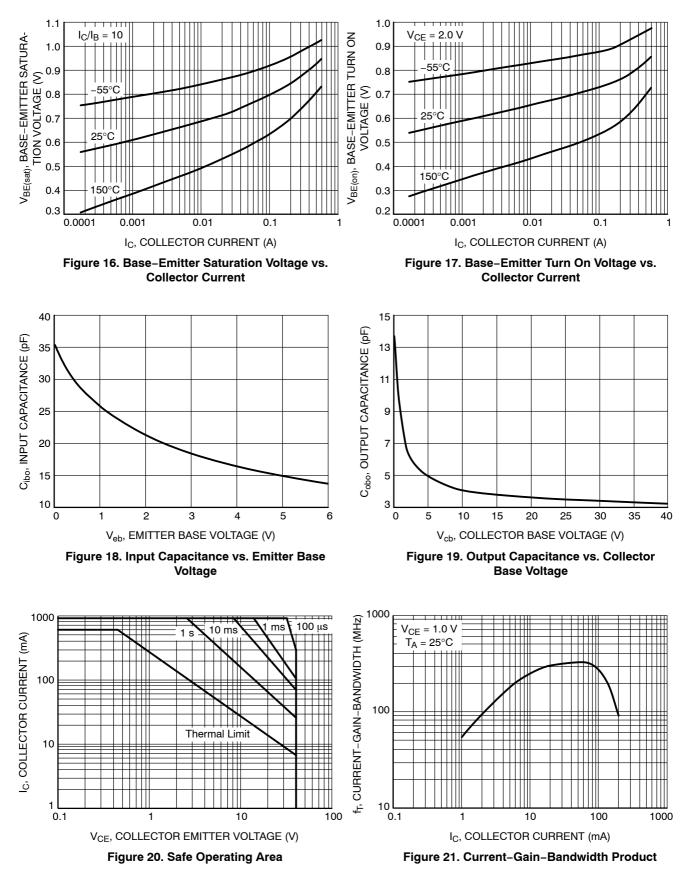
This group of graphs illustrates the relationship between  $h_{fe}$  and other "h" parameters for this series of transistors. To obtain these curves, a high–gain and a low–gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.



**STATIC CHARACTERISTICS** 

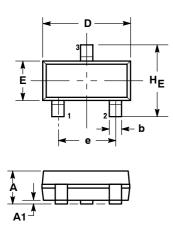


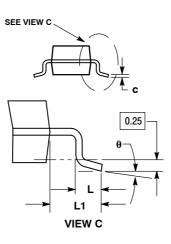
## STATIC CHARACTERISTICS



#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP** 





NOTES

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2.

1992. 2. CONTROLLING DIMENSION: INCH. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM 3

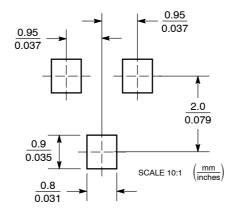
THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. 4

PROT	RUSIONS OB GATE BURRS.			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
с	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
ΗE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6: PIN 1. BASE EMITTER 2 З.

COLLECTOR

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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